	Туре	L#	Hits	Search Text	DBs
1	BRS	L1	1273	257/724.ccls.	US-PGPUB; USPAT; USOCR
2	BRS	L2	1809	257/723.ccls.	US-PGPUB; USPAT; USOCR
3	BRS	L3	1911	257/787.ccls.	US-PGPUB; USPAT; USOCR
4	BRS	L5	135	L2 and inductor and capacitor	US-PGPUB; USPAT; USOCR
5	BRS	L6	67	L3 and inductor and capacitor	US-PGPUB; USPAT; USOCR
6	BRS	L8	429	257/723.ccls.	EPO; JPO; DERWENT; IBM_TDB
7	BRS	L7	498	257/724.ccls.	EPO; JPO; DERWENT; IBM_TDB
8	BRS	L9	0	L7 and inductor and capacitor	US-PGPUB; USPAT; USOCR
9	BRS	L4	142	L1 and inductor and capacitor	US-PGPUB; USPAT; USOCR
10	BRS	L10	25	((chip or die) and substrate and passive and inductor and capacitor and (insulating ordielectric)).clm.	US-PGPUB

	Туре	L#	Hits	Search Text	DBs
11	BRS	L11		257/774.ccls.	US-PGPUB; USPAT; USOCR
12	BRS	L12	82	L11 and inductor and capacitor	US-PGPUB; USPAT; USOCR
13	BRS	L13	36	L12 and wafer	US-PGPUB; USPAT; USOCR